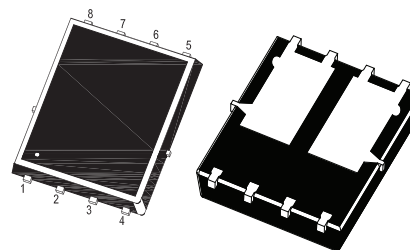
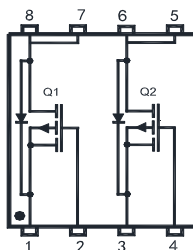


Dual P-Channel Enhancement Mode MOSFET
Features

- Low On-Resistance
- Halogen and Antimony Free(HAF), RoHS compliant



Q1:1.Source 2.Gate 7.Drain 8.Drain
 Q2:3.Source 4.Gate 5.Drain 6.Drain
 DFN5060 Plastic Package

Key Parameters(Q1/Q2)

Parameter	Value	Unit
BV_{DSS}	30	V
$R_{DS(ON)} \text{ Max}$	15 @ $V_{GS} = 10 \text{ V}$	m Ω
	18.5 @ $V_{GS} = 4.5 \text{ V}$	
$V_{GS(th)} \text{ typ}$	1.5	V
$Q_g \text{ typ}$	48 @ $V_{GS} = 10 \text{ V}$	nC

Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)(Q1/Q2)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$-V_{DS}$	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	$-I_D$	34	A
		21	
Peak Drain Current, Pulsed ¹⁾	$-I_{DM}$	140	A
Single-Pulse Avalanche Current	$-I_{AS}$	28.7	A
Single-Pulse Avalanche Energy ²⁾	E_{AS}	41	mJ
Power Dissipation	P_D	25	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Characteristics(Q1/Q2)

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	5	$^\circ\text{C/W}$
Thermal Resistance from Junction to Ambient ³⁾	$R_{\theta JA}$	65	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width $\leq 100 \mu\text{s}$, Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.

²⁾ Limited by $T_{J(MAX)}$, starting $T_J = 25^\circ\text{C}$, $L = 0.1 \text{ mH}$, $R_g = 25 \Omega$, $-I_{AS} = 28.7 \text{ A}$, $V_{GS} = 10 \text{ V}$.

³⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified(Q1/Q2)

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $-I_D = 250\ \mu\text{A}$	$-BV_{DS}$	30	-	-	V
Drain-Source Leakage Current at $-V_{DS} = 30\ \text{V}$	$-I_{DSS}$	-	-	1	μA
Gate Leakage Current at $V_{GS} = \pm 20\ \text{V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}$, $-I_D = 250\ \mu\text{A}$	$-V_{GS(th)}$	1	-	2.5	V
Drain-Source On-State Resistance at $-V_{GS} = 10\ \text{V}$, $-I_D = 15\ \text{A}$ at $-V_{GS} = 4.5\ \text{V}$, $-I_D = 10\ \text{A}$	$R_{DS(on)}$	- -	13.6 -	15 18.5	m Ω
DYNAMIC PARAMETERS					
Forward Transconductance at $-V_{DS} = 5\ \text{V}$, $-I_D = 10\ \text{A}$	g_{FS}	-	22	-	S
Gate Resistance at $V_{GS} = 0\ \text{V}$, $V_{DS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	R_g	-	4.2	-	Ω
Input Capacitance at $-V_{DS} = 15\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	C_{iss}	-	2515	-	pF
Output Capacitance at $-V_{DS} = 15\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	C_{oss}	-	247	-	pF
Reverse Transfer Capacitance at $-V_{DS} = 15\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	C_{rss}	-	191	-	pF
Total Gate Charge at $-V_{GS} = 10\ \text{V}$, $-V_{DS} = 15\ \text{V}$, $-I_D = 15\ \text{A}$ at $-V_{GS} = 4.5\ \text{V}$, $-V_{DS} = 15\ \text{V}$, $-I_D = 15\ \text{A}$	Q_g	- -	48 22	- -	nC
Gate-Source Charge at $-V_{GS} = 10\ \text{V}$, $-V_{DS} = 15\ \text{V}$, $-I_D = 15\ \text{A}$	Q_{gs}	-	9	-	nC
Gate-Drain Charge at $-V_{GS} = 10\ \text{V}$, $-V_{DS} = 15\ \text{V}$, $-I_D = 15\ \text{A}$	Q_{gd}	-	8	-	nC
Turn-On Delay Time at $-V_{GS} = 10\ \text{V}$, $-V_{DS} = 15\ \text{V}$, $-I_D = 15\ \text{A}$, $R_g = 3.3\ \Omega$	$t_{d(on)}$	-	15	-	ns
Turn-On Rise Time at $-V_{GS} = 10\ \text{V}$, $-V_{DS} = 15\ \text{V}$, $-I_D = 15\ \text{A}$, $R_g = 3.3\ \Omega$	t_r	-	35	-	ns
Turn-Off Delay Time at $-V_{GS} = 10\ \text{V}$, $-V_{DS} = 15\ \text{V}$, $-I_D = 15\ \text{A}$, $R_g = 3.3\ \Omega$	$t_{d(off)}$	-	30	-	ns
Turn-Off Fall Time at $-V_{GS} = 10\ \text{V}$, $-V_{DS} = 15\ \text{V}$, $-I_D = 15\ \text{A}$, $R_g = 3.3\ \Omega$	t_f	-	5	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $-I_S = 1\ \text{A}$, $V_{GS} = 0\ \text{V}$	$-V_{SD}$	-	-	1.2	V
Body-Diode Continuous Current	$-I_S$	-	-	34	A
Body-Diode Continuous Current, Pulsed	$-I_{SM}$	-	-	140	A
Body Diode Reverse Recovery Time at $-I_S = 15\ \text{A}$, $di/dt = 100\ \text{A} / \mu\text{s}$	t_{rr}	-	17.5	-	ns
Body Diode Reverse Recovery Charge at $-I_S = 15\ \text{A}$, $di/dt = 100\ \text{A} / \mu\text{s}$	Q_{rr}	-	11.5	-	nC

Electrical Characteristics Curves(Q1/Q2)

Fig. 1 Typical Output Characteristics

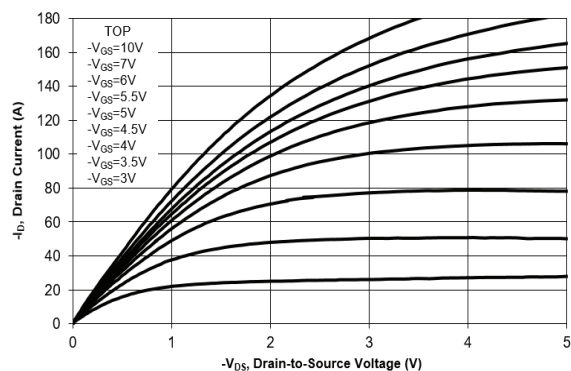


Fig. 2 Typical Transfer Characteristics

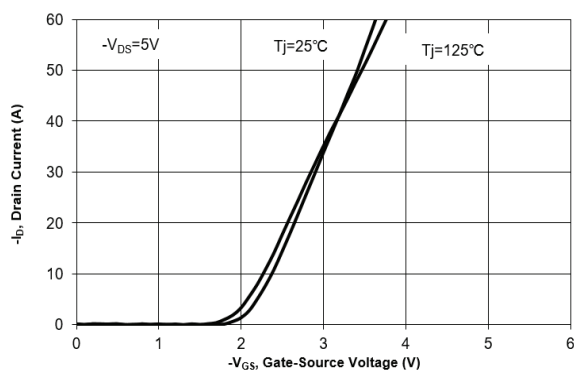


Fig. 3 on-Resistance vs. Drain Current

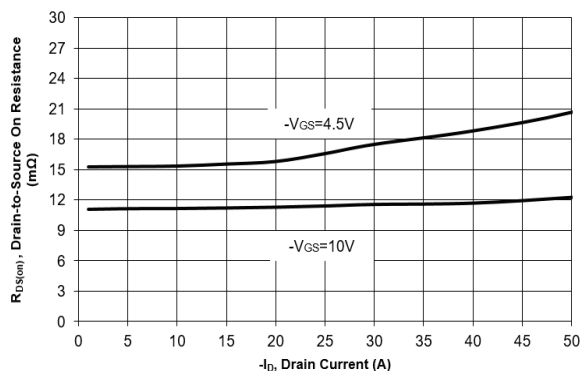


Fig. 4 on-Resistance vs. Gate to Source Voltage

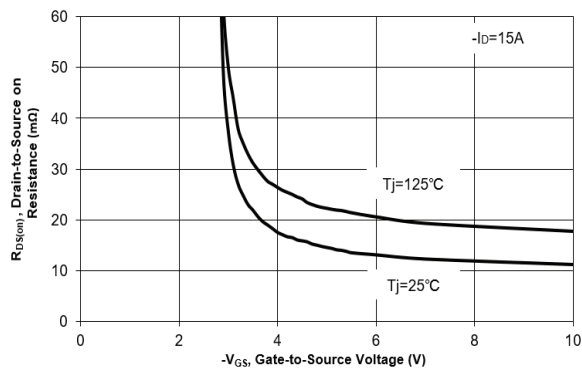


Fig. 5 on-Resistance vs. Tj

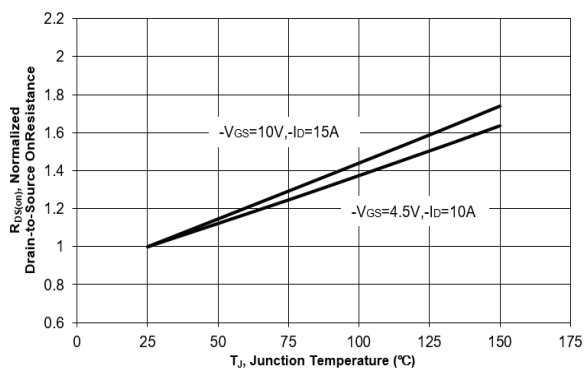
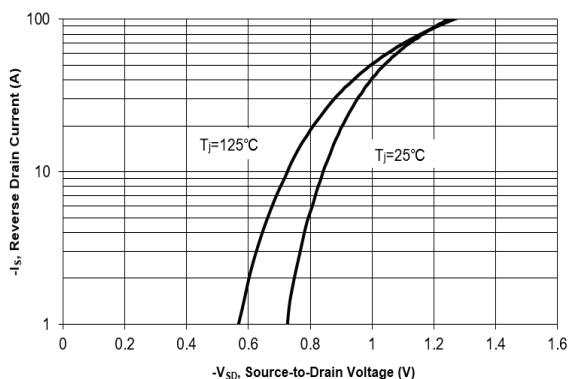


Fig. 6 Typical Body-Diode Forward Characteristics



Electrical Characteristics Curves(Q1/Q2)

Fig. 7 Typical Junction Capacitance

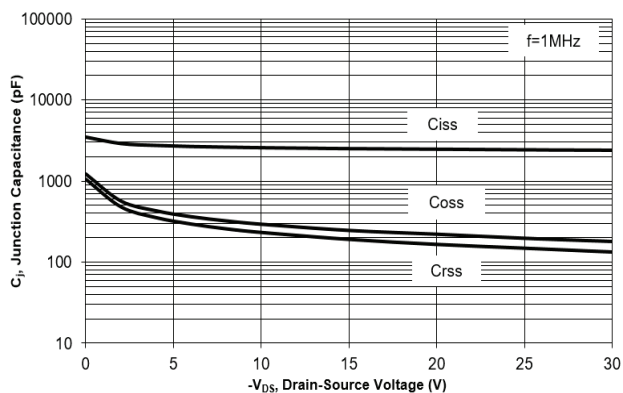


Fig. 8 Drain-Source Leakage Current vs. T_J

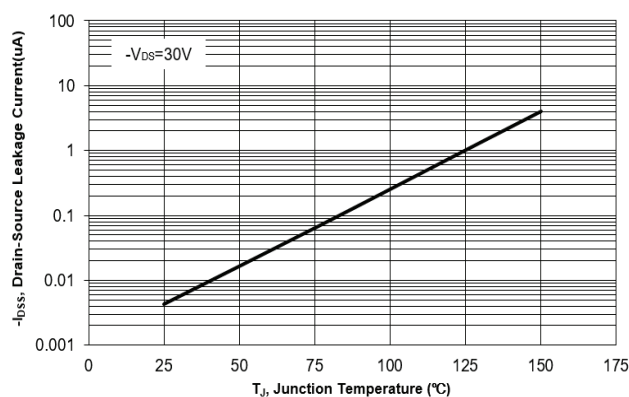


Fig. 9 $V_{(BR)DSS}$ vs. Junction Temperature

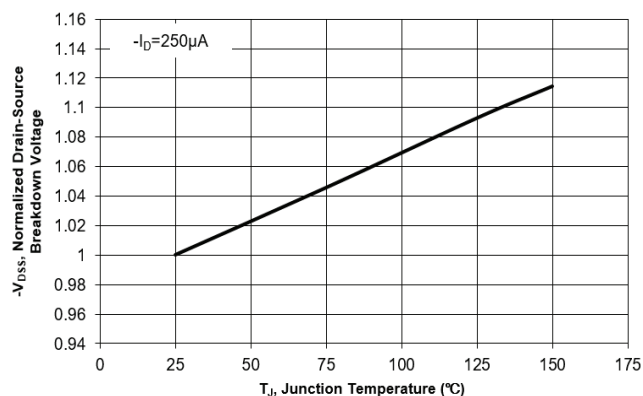


Fig. 10 Gate Threshold Variation vs. T_J

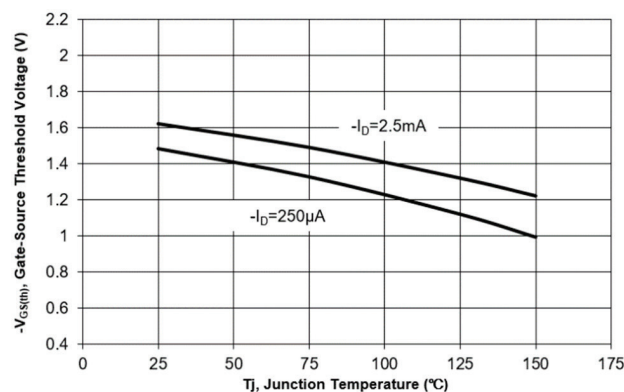


Fig. 11 Gate Charge

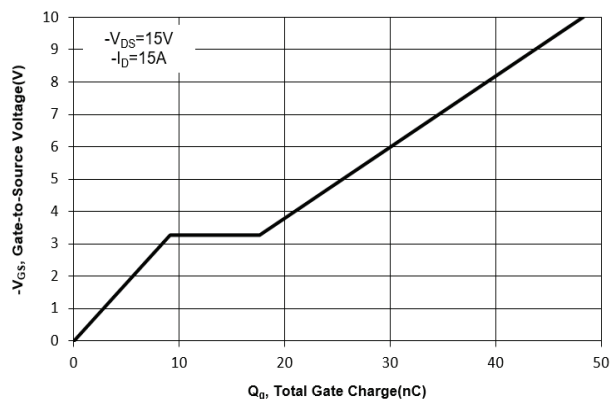


Fig. 12 Safe Operation Area

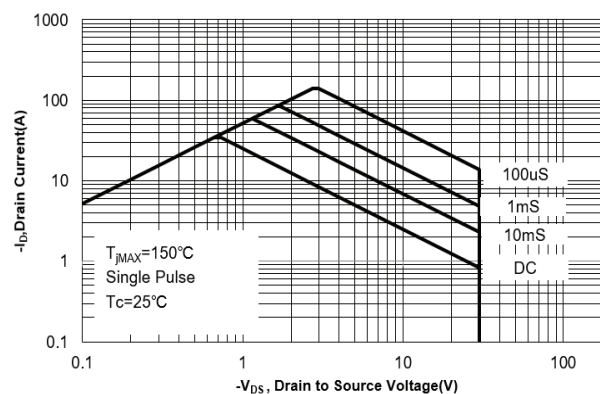


Fig. 13 Normalized Maximum Transient Thermal Impedance($z_{\theta JC}$)

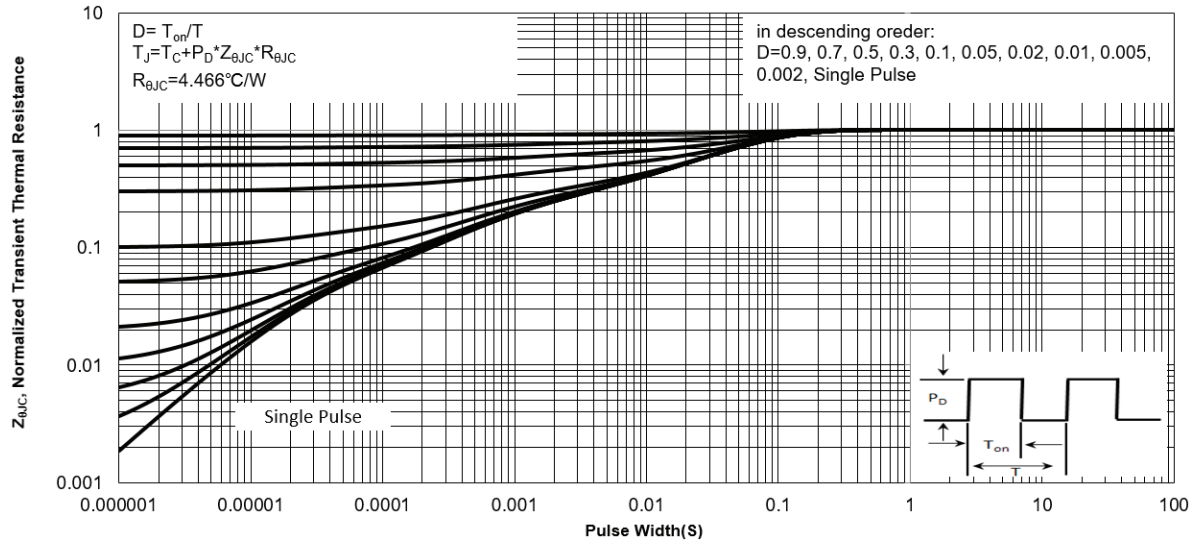
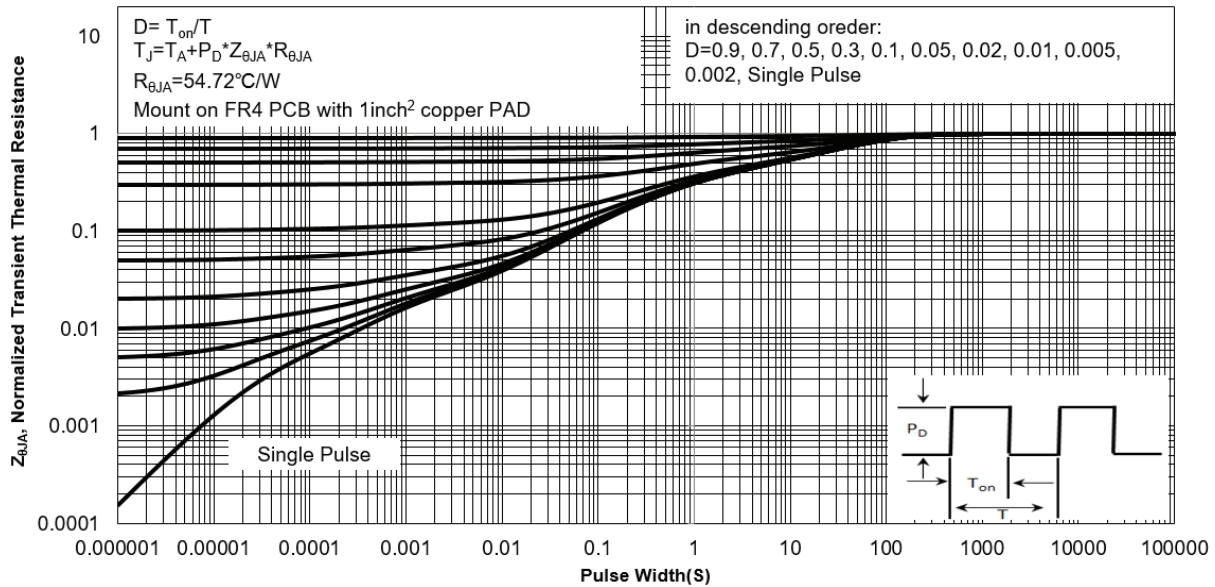


Fig. 14 Normalized Maximum Transient Thermal Impedance($z_{\theta JA}$)



Test Circuits(Q1/Q2)

Fig.1-1 Switching times test circuit

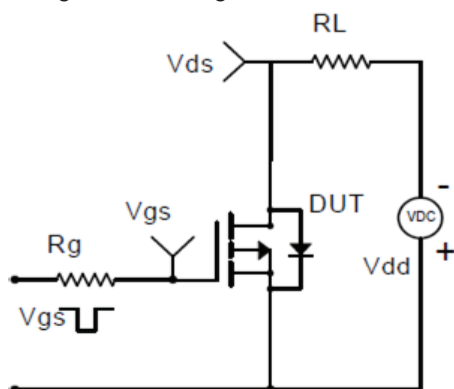


Fig.1-2 Switching Waveform

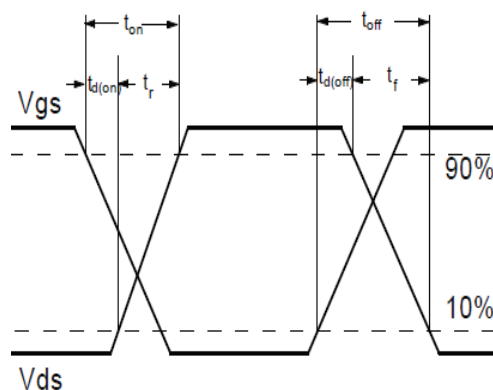


Fig.2-1 Gate charge test circuit

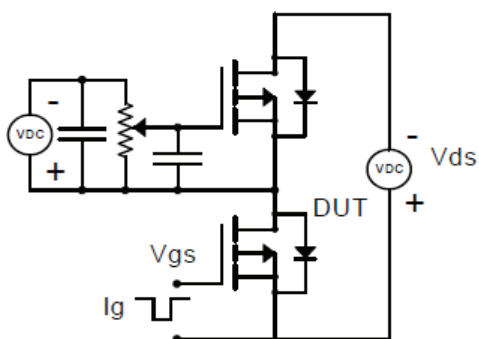


Fig.2-2 Gate charge waveform

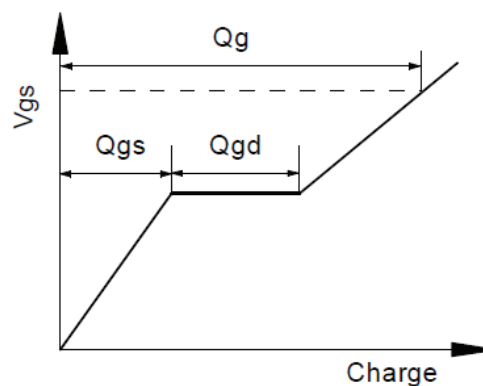


Fig.3-1 Avalanche test circuit

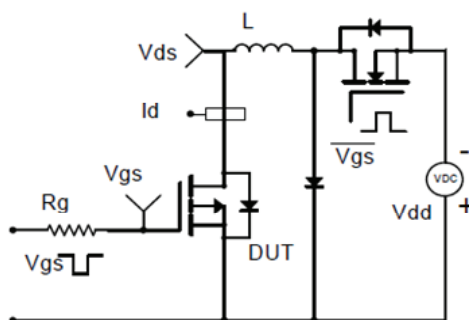
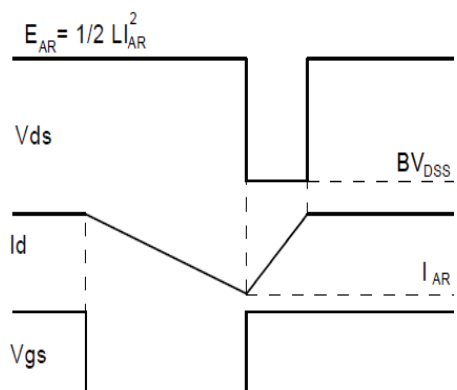
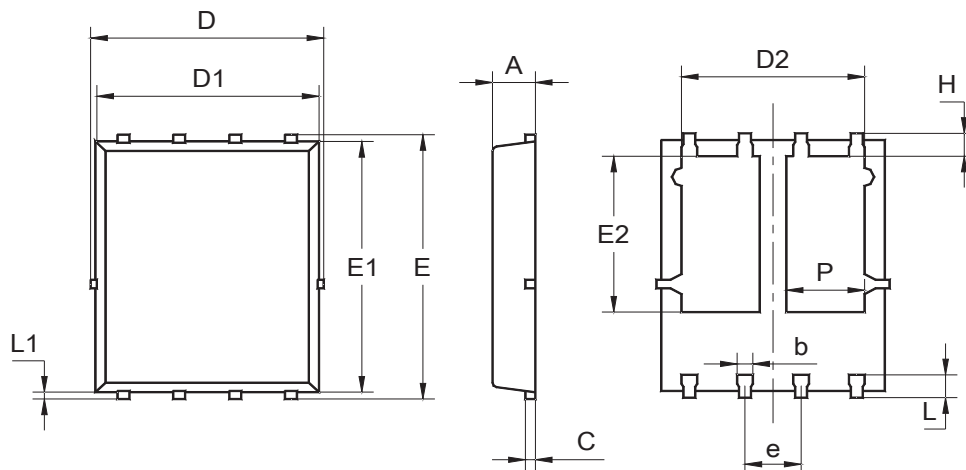


Fig.3-2 Avalanche waveform



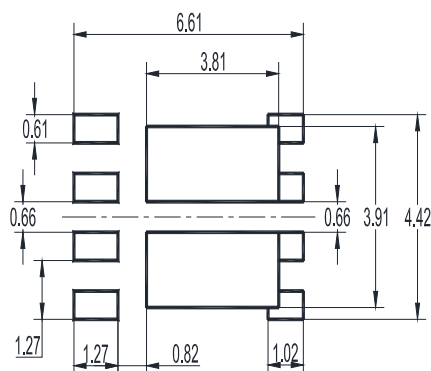
Package Outline Dimensions (Units: mm)

DFN5060



Unit	A	b	C	D	D1	D2	E	E1	E2	e	L	L1	H	P
mm	1.12 0.9	0.51 0.33	0.34 0.11	5.26 4.7	5.1 4.7	4.5 3.56	6.25 5.75	6 5.6	3.66 3.18	1.37 1.17	0.71 0.35	0.2 0.06	0.71 0.35	2.3 1.7

Recommended Soldering Footprint



Packing information

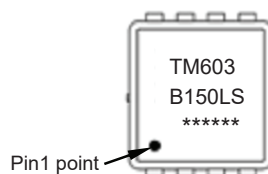
Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN5060	12	8 ± 0.1	0.315 ± 0.004	330	13	5,000

Marking information

" TM603B150LS " = Part No.

" ***** " = Date Code Marking

Font type: Arial



Disclaimer: Our company reserve the right to make modifications, enhancements, improvements, corrections or other changes to improve product design, functions and reliability, anytime without notice.